





SN74LV244A

### SCLS383R - SEPTEMBER 1997 - REVISED AUGUST 2023

## SN74LV244A Octal Buffers and Drivers With 3-State Outputs

#### 1 Features

- V<sub>CC</sub> operation of 2 V to 5.5 V
- Maximum t<sub>pd</sub> of 6.5 ns at 5 V
- Typical V<sub>OLP</sub> (output ground bounce) <0.8 V at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C
- Typical V<sub>OHV</sub> (output V<sub>OH</sub> undershoot)  $>2.3 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Support mixed-mode voltage operation on all ports
- I<sub>off</sub> supports partial-power-down mode operation
- Latch-up performance exceeds 250-mA per JESD

## 2 Applications

- Servers and network switches
- LED displays
- Telecom infrastructure
- Motor-drive control boards

## 3 Description

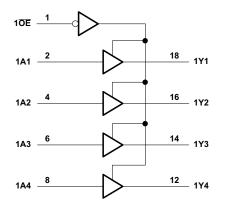
The SN74LV244A octal buffers and line drivers are designed for 2-V to 5.5-V V<sub>CC</sub> operation.

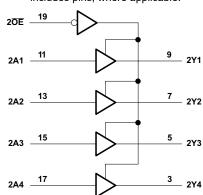
The SN74LV244A devices are designed specifically to improve both performance and density of the 3state memory address drivers, clock drivers, and busoriented receivers and transmitters. These devices are organized as two 4-bit line drivers with separate output-enable  $(\overline{OE})$  inputs.

### **Package Information**

PART NUMBER	PACKAGE <sup>1</sup>	PACKAGE SIZE <sup>2</sup>
	DB (SSOP, 20)	7.2 mm × 7.8 mm
	DGV (TVSOP, 20)	5.00 mm × 6.4 mm
	DW (SOIC, 20)	12.80 mm × 10.3 mm
SN74LV244A	NS (SO, 20)	12.60 mm × 5.30 mm
SIN/4LV244A	PW (TSSOP, 20)	6.50 mm × 7.8 mm
	RGY (VQFN, 20)	4.5 mm × 3.50 mm
	RKS (VQFN, 20)	4.50 mm × 2.50 mm
	DGS (VSSOP, 20)	5.10 mm × 4.9 mm

- For all available packages, see the orderable addendum at the end of the data sheet.
- The package size (length × width) is a nominal value and includes pins, where applicable.





Logic Diagram (Positive Logic)



## **Table of Contents**

1 Features1	8.1 Overview	10
2 Applications1	8.2 Functional Block Diagram	
3 Description1	8.3 Feature Description	
4 Revision History2	8.4 Device Functional Modes	
5 Pin Configuration and Functions3	9 Application and Implementation	12
6 Specifications4	9.1 Application Information	12
6.1 Absolute Maximum Ratings4	9.2 Typical Application	
6.2 ESD Ratings4	9.3 Power Supply Recommendations	15
6.3 Recommended Operating Conditions5	9.4 Layout	15
6.4 Thermal Information5	10 Device and Documentation Support	16
6.5 Electrical Characteristics6	10.1 Documentation Support	16
6.6 Noise Characteristics6	10.2 Receiving Notification of Documentation Updates	
6.7 Operating Characteristics6	10.3 Support Resources	16
6.8 Switching Characteristics: V <sub>CC</sub> = 2.5 V ± 0.2 V7	10.4 Trademarks	16
6.9 Switching Characteristics: V <sub>CC</sub> = 3.3 V ± 0.3 V7	10.5 Electrostatic Discharge Caution	16
6.10 Switching Characteristics: V <sub>CC</sub> = 5 V ± 0.5 V7	10.6 Glossary	16
6.11 Typical Characteristics8	11 Mechanical, Packaging, and Orderable	
7 Parameter Measurement Information9	Information	16
8 Detailed Description10		

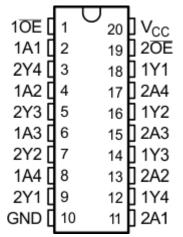
## **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision Q (March 2023) to Revision R (August 2023)	Page
•	Added DB package and replaced body size with package size in Package Information table	
•	Updated thermal values for PW package from RθJA = 102.6 to 128.2, RθJC(top) = 36.7 to 70.5, RθJB =	
	to 79.3, $\Psi$ JT = 2.4 to 23.4, $\Psi$ JB = 53.1 to 78.9, all values in °C/W	5
C	hanges from Revision P (January 2023) to Revision Q (March 2023)	Page
•	Updated thermal values for DB package from RθJA = 94.7 to 118.2, RθJC(top) = 56.7 to 77.2, RθJB = 473, ΨJT = 18.7 to 42.2, ΨJB = 49.5 to 72.6, all values in °C/W	
•	Updated thermal values for DW package from RθJA = 79.4 to 102.3 RθJC(top) = 43.8 to 69.9, RθJB = 470.8, ΨJT = 18.8 to 46.4, ΨJB = 46.7 to 70.4, all values in °C/W	47.2 to
•	Updated thermal values for NS package from RθJA = 76.9 to 108.1, RθJC(top) = 43.4 to 73.9, RθJB = 473.1, ΨJT = 17.0 to 44.1, ΨJB = 44.1 to 72.8, all values in °C/W	44.5 to



## **5 Pin Configuration and Functions**





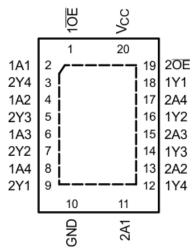


Figure 5-2. RGY and RKS Package, 20-Pin VQFN With Exposed Thermal Pad (Top View)

Table 5-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.	ITPE(')	DESCRIPTION
1A1	2	I	Input
1A2	4	I	Input
1A3	6	I	Input
1A4	8	I	Input
1 ŌĒ	1	I	Output enable
1Y1	18	0	Output
1Y2	16	0	Output
1Y3	14	0	Output
1Y4	12	0	Output
2A1	11	I	Input
2A2	13	ı	Input
2A3	15	ı	Input
2A4	17	ı	Input
2 OE	19	I	Output enable
2Y1	9	0	Output
2Y2	7	0	Output
2Y3	5	0	Output
2Y4	3	0	Output
GND	10	_	Ground
V <sub>CC</sub>	20	_	Power pin
Thermal pad <sup>(2)</sup>	)	_	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.

<sup>(1)</sup> Signal Types: I = Input, O = Output, I/O = Input or Output

<sup>(2)</sup> RKS package only



## **6 Specifications**

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	7	V
VI	Input voltage <sup>(2)</sup>	put voltage <sup>(2)</sup>			
Vo	Voltage range applied to any output in the	oltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>			
Vo	Output voltage <sup>(2) (3)</sup>	-0.5	V <sub>CC</sub> + 0.5	V	
I <sub>IK</sub>	Input clamp current	V <sub>1</sub> < 0		-20	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
Io	Continuous output current	V <sub>O</sub> = 0 to V <sub>CC</sub>		±35	mA
	Continuous current through V <sub>CC</sub> or GND	·		±70	mA
Tj	Junction temperature	-65	150	°C	
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	\/
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

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<sup>(2)</sup> The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

This value is limited to 5.5-V maximum.



## **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2	5.5	V
		V <sub>CC</sub> = 2 V	1.5		
	Library Laurel State of the sta	V <sub>CC</sub> = 2.3 V to 2.7 V	V <sub>CC</sub> × 0.7		V
$V_{IH}$	High-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V	V <sub>CC</sub> × 0.7		V
		V <sub>CC</sub> = 4.5 V to 5.5 V	V <sub>CC</sub> × 0.7		
		V <sub>CC</sub> = 2 V		0.5	
V <sub>IL</sub>	Lave lavel in motoralta ma	V <sub>CC</sub> = 2.3 V to 2.7 V		V <sub>CC</sub> × 0.3	V
	Low-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V		V <sub>CC</sub> × 0.3	V
		V <sub>CC</sub> = 4.5 V to 5.5 V		V <sub>CC</sub> × 0.3	
VI	Input voltage	,	0	5.5	V
	Output voltage	High or low state	0	V <sub>CC</sub>	V
Vo		3-state	0	5.5	V
		V <sub>CC</sub> = 2 V		-50	μA
	I Barba Lancel and and an annual A	V <sub>CC</sub> = 2.3 V to 2.7 V		-2	
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 3 V to 3.6 V		-8	mA
		V <sub>CC</sub> = 4.5 V to 5.5 V		-16	
		V <sub>CC</sub> = 2 V		50	μA
	Lave lavel autout assessed	V <sub>CC</sub> = 2.3 V to 2.7 V		2	
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 3 V to 3.6 V		8	mA
		V <sub>CC</sub> = 4.5 V to 5.5 V		16	
		V <sub>CC</sub> = 2.3 V to 2.7 V		200	
Δt/Δν	Input transition rise or fall rate	rate $V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		100	ns/V
		V <sub>CC</sub> = 4.5 V to 5.5 V		20	
T <sub>A</sub>	Operating free-air temperature	1	-40	125	°C

<sup>(1)</sup> All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

## **6.4 Thermal Information**

		SN74LV244A								
THERMAL METRIC <sup>(1)</sup>		DB (SSOP)	DGV (TVSOP)	DW (SOIC)	NS (SO)	PW (TSSOP)	RGY (VQFN)	RKS (VQFN)	DGS (VSSOP)	UNIT
		20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	118.2	115.9	102.3	108.1	128.2	34.9	75.2	125.5	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	77.2	31.1	69.9	73.9	70.5	43.1	79.4	80.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	73	57.4	70.8	73.1	79.3	12.7	47.8	63.8	°C/W
Ψ <sub>Ј</sub> Τ	Junction-to-top characterization parameter	42.2	1.0	46.4	44.1	23.4	0.9	14.6	8.4	°C/W
ΨЈВ	Junction-to-board characterization parameter	72.6	56.7	70.4	72.8	78.9	12.8	47.8	79.9	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	7.8	31.5	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.



## **6.5 Electrical Characteristics**

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP	MAX	UNIT
		I <sub>OH</sub> = -50 μA	2 V to 5.5 V	V <sub>CC</sub> - 0.1			
V <sub>OH</sub>	High level output voltage	I <sub>OH</sub> = -2 mA	2.3 V	2			٧
		I <sub>OH</sub> = -8 mA	3 V	2.48			
		I <sub>OH</sub> = 16 mA	4.5 V	3.8			
		Ι <sub>ΟL</sub> = 50 μΑ	2 V to 5.5 V			0.1	
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA	2.3 V			0.4	V
		I <sub>OL</sub> = 8 mA	3 V			0.44	
		I <sub>OL</sub> = 16 mA	4.5 V			0.55	
I <sub>1</sub>	Input leakage current	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±1	μA
I <sub>OZ</sub>	Off-State (High-Impedance State) Output Current (of a 3-State Output)	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5 V			±5	μA
I <sub>CC</sub>	Supply current	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			20	μA
I <sub>off</sub>	Input/Output Power-Off Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0 to 5.5 V	0			5	μA
C <sub>i</sub>	Input capacitance	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		2.3		pF

## **6.6 Noise Characteristics**

 $V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}^{(1)}$ 

		MIN	TYP	MAX	UNIT
V <sub>OL(P)</sub>	Quiet output, maximum dynamic		0.55		V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic		-0.5		V
V <sub>OH(V)</sub>	Quiet output, minimum dynamic		2.9		V
V <sub>IH(D)</sub>	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

<sup>(1)</sup> Characteristics are for surface-mount packages only.

## **6.7 Operating Characteristics**

 $T_A = 25^{\circ}C$ 

	PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	TYP	UNIT
_	Power discination canacitance	$C_1 = 50 \text{ pF f} = 10 \text{ MHz}$	3.3 V	14	pF
Opd	Power dissipation capacitance	OL - 30 pr 1 - 10 MHZ	5 V	16	ρı

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## 6.8 Switching Characteristics: $V_{CC}$ = 2.5 V ± 0.2 V

over operating free-air temperature range (unless otherwise noted), (see Load Circuit and Voltage Waveforms)

PARAMETE	FROM	то	LOAD	,, (	25°C		-40°	C to 125°C		UNIT	
R	(INPUT)	(OUTPUT)	CAP	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
4	А	Y	C <sub>L</sub> = 15 pF		7.5	12.5	1		15	ns	
t <sub>pd</sub>	^	'	C <sub>L</sub> = 50 pF		9.5	15.3	1		18	115	
4	ŌĒ	Υ	C <sub>L</sub> = 15 pF		8.9	14.6	1		17	no	
t <sub>en</sub>	UE	OE	,	C <sub>L</sub> = 50 pF		10.8	17.8	1		21	ns
4	ŌĒ	Υ	C <sub>L</sub> = 15 pF		9.1	14.1	1		16	no	
t <sub>dis</sub>	OL	'	C <sub>L</sub> = 50 pF		13.4	19.2	1		21	ns	
t <sub>sk(o)</sub>			C <sub>L</sub> = 50 pF			2			2	ns	

## 6.9 Switching Characteristics: $V_{CC}$ = 3.3 V $\pm$ 0.3 V

over operating free-air temperature range (unless otherwise noted), (see Load Circuit and Voltage Waveforms)

PARAMETE R	FROM	TO (OUTPUT)	LOAD		25°C		-40°	UNIT		
	(INPUT)		CAP	MIN	TYP	MAX	MIN	TYP	MAX	ONII
		Y	C <sub>L</sub> = 15 pF		5.4	8.4	1		10	
t <sub>pd</sub>	А	Y	C <sub>L</sub> = 50 pF		6.8	11.9	1		13.5	ns
4	en ŌĒ	Y	C <sub>L</sub> = 15 pF		6.3	10.6	1		12.5	
l <sup>e</sup> n		ř	C <sub>L</sub> = 50 pF		7.8	14.1	1		16 ns	
4	ŌĒ	Y	C <sub>L</sub> = 15 pF		7.6	11.7	1		13	no
t <sub>dis</sub> OE	OE .	ľ	C <sub>L</sub> = 50 pF		11	16	1		18	ns
t <sub>sk(o)</sub>			C <sub>L</sub> = 50 pF			1.5			1.5	ns

## 6.10 Switching Characteristics: $V_{CC} = 5 V \pm 0.5 V$

over operating free-air temperature range (unless otherwise noted), (see Load Circuit and Voltage Waveforms)

PARAMETE R	FROM	TO (OUTPUT)	LOAD CAP		25°C		-40°C to 125°C			UNIT	
	(INPUT)			MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
<b>.</b>	A	Υ	C <sub>L</sub> = 15 pF		3.9	5.5	1		6.5	no	
t <sub>pd</sub>		Ť	C <sub>L</sub> = 50 pF		4.9	7.5	1		8.5	ns	
t <sub>en</sub>	Υ	C <sub>L</sub> = 15 pF		4.5	7.3	1		8.5	no		
	Ť	C <sub>L</sub> = 50 pF		5.6	9.3	1		10.5	ns		
+	ŌĒ	Y	C <sub>L</sub> = 15 pF		6.5	12.2	1		13.5	no	
t <sub>dis</sub>	OE	Ť	C <sub>L</sub> = 50 pF		8.8	14.2	1		15.5	ns	
t <sub>sk(o)</sub>			C <sub>L</sub> = 50 pF			1			1	ns	



## 6.11 Typical Characteristics

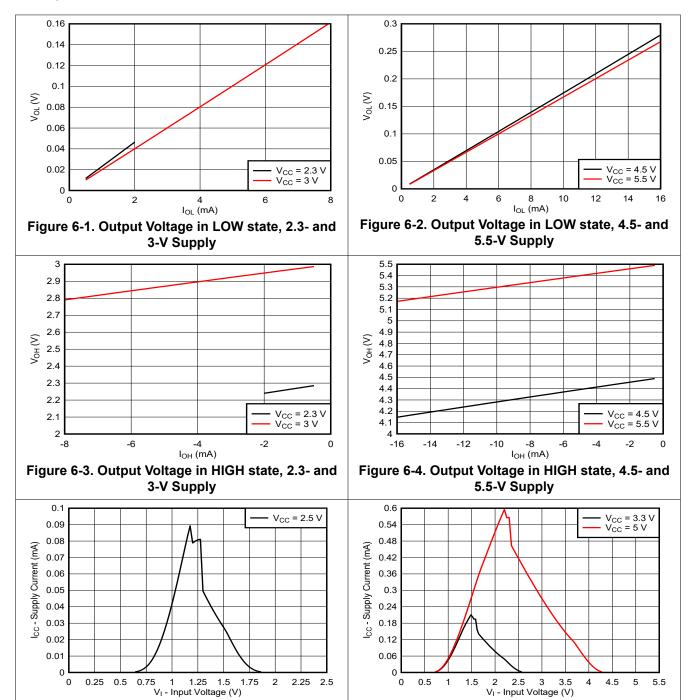


Figure 6-5. Supply Current across Input Voltage,

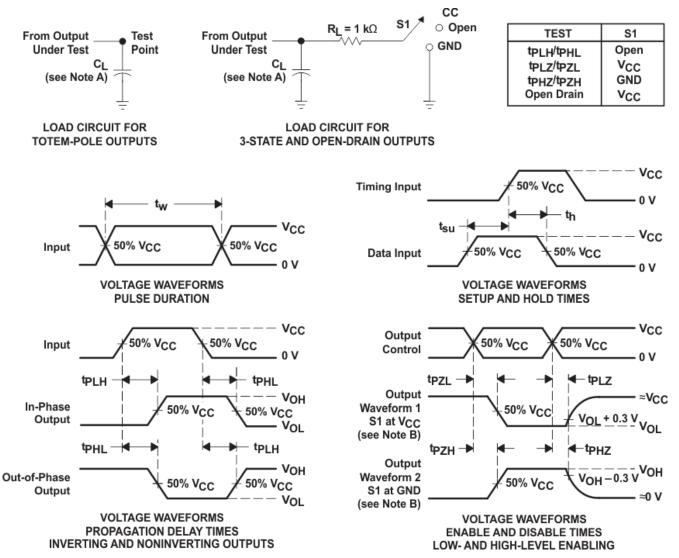
2.5-V Supply

Figure 6-6. Supply Current across Input Voltage,

3.3- and 5-V Supply



## 7 Parameter Measurement Information



- A. C<sub>L</sub> includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O = 50 \Omega$ ,  $t_r \leq 3$  ns.  $t_f \leq 3$  ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PHL}$  and  $t_{PLH}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

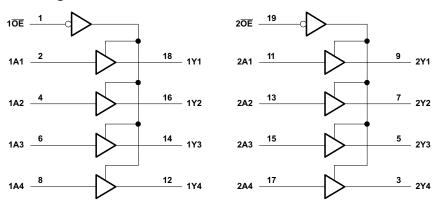
Figure 7-1. Load Circuit and Voltage Waveforms

## **8 Detailed Description**

#### 8.1 Overview

The SN74LV244 devices are octal buffers grouped in fours, with each group having its own enable pin. The LV family supports high current drive of about 16 mA, thus making it suitable for driving digital signals over longer board lengths. This device is generally used to buffer or incorporate delays between the signals between two microcontroller or peripheral devices.

## 8.2 Functional Block Diagram



## 8.3 Feature Description

#### 8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a  $10-k\Omega$  resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

## 8.3.2 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law  $(R = V \div I)$ .

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can

be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a  $10-k\Omega$  resistor, however, is recommended and will typically meet all requirements.

#### 8.3.3 Partial Power Down (I<sub>off</sub>)

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I<sub>off</sub> specification in the *Electrical Characteristics* table.

#### 8.3.4 Clamp Diode Structure

Figure 8-1 shows the inputs and outputs to this device have negative clamping diodes only.

#### **CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

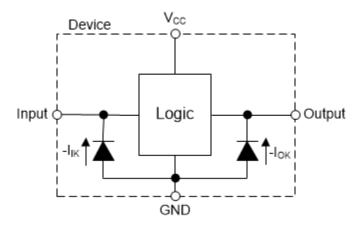


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

### 8.4 Device Functional Modes

The SN74LV244A devices are organized as two 4-bit line drivers with separate output-enable  $(\overline{OE})$  inputs. When  $\overline{OE}$  is low, the device passes data from the A inputs to the Y outputs. When  $\overline{OE}$  is high, the outputs are in the high-impedance state. To ensure the high-impedance state during power up or power down,  $\overline{OE}$  must be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

INPU	OUTPUTS <sup>(2)</sup>	
ŌĒ	Α	Υ
L	L	L
L	Н	Н
Н	X	Z

**Table 8-1. Function Table** 

- (1) H = High Voltage Level, L = Low Voltage Level, X = Do Not Care
- (2) H = Driving High, L = Driving Low, Z = High Impedance State



## 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

## 9.1 Application Information

The SN74LV244A device can be used as an 8-channel buffer to drive signals from one controller to another device. Buffers are typically used for signals running on long traces on printed circuit boards or going through connectors linking two printed circuit boards together. Buffers are also used to create delay between the lines to match the edges of two clock or data signals. The high-current capability of the SN74LV244A device also allows a controller to drive LEDs up to 16 mA.

## 9.2 Typical Application

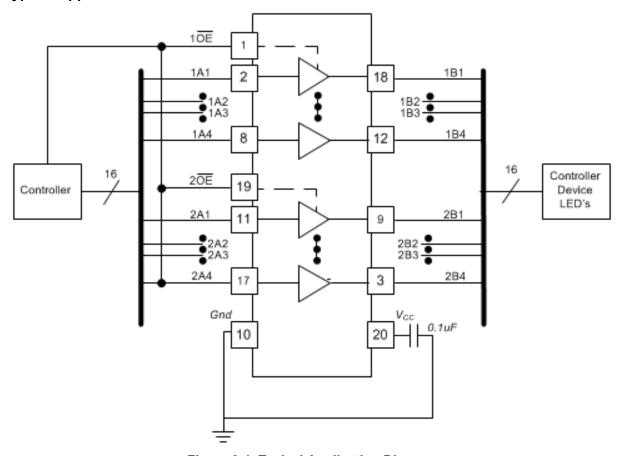


Figure 9-1. Typical Application Diagram

#### 9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV244A plus the maximum static supply current, I<sub>CC</sub>, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is

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provided by the positive supply source. Be sure to not exceed the maximum total current through  $V_{CC}$  listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV244A plus the maximum supply current, I<sub>CC</sub>, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV244A can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV244A can drive a load with total resistance described by  $R_L \ge V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear* and Logic (SLL) Packages and Devices.

#### **CAUTION**

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

#### 9.2.2 Input Considerations

Input signals must cross  $V_{IL(max)}$  to be considered a logic LOW, and  $V_{IH(min)}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV244A (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74LV244A has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the Feature Description section for additional information regarding the inputs for this device.

#### 9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V<sub>CC</sub> or ground.

Refer to the Feature Description section for additional information regarding the outputs for this device.

#### 9.2.4 Detailed Design Procedure

- Add a decoupling capacitor from V<sub>CC</sub> to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V<sub>CC</sub> and GND pins. An example layout is shown in the *Layout* section.
- 2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV244A to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)}) \Omega$ . Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in M $\Omega$ ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

#### 9.2.5 Application Curve

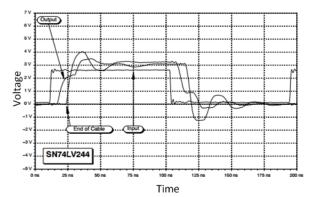


Figure 9-2. SN74LV244A Transient response

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## 9.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Absolute Maximum Ratings* section. Each  $V_{CC}$  terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1- $\mu$ F capacitor; if there are multiple  $V_{CC}$  terminals, then TI recommends a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor for each power terminal. Multiple bypass capacitors can be paralleled to reject different frequencies of noise. Frequencies of 0.1  $\mu$ F and 1  $\mu$ F are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

### 9.4 Layout

### 9.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

#### 9.4.2 Layout Example

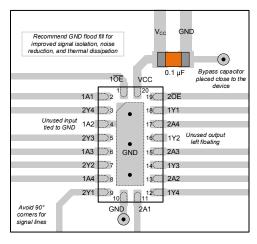


Figure 9-3. Layout Example for the SN74LV244A in the RKS Package



## 10 Device and Documentation Support

## **10.1 Documentation Support**

### 10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application notes
- Texas Instruments, Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices

## 10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 10.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 10.4 Trademarks

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## 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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## **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV244ADBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244ADBRE4	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244ADBRG4	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244ADGSR	ACTIVE	VSSOP	DGS	20	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L244A	Samples
SN74LV244ADGVR	ACTIVE	TVSOP	DGV	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244ADW	OBSOLETE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 125	LV244A	
SN74LV244ADWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244ADWRG4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244ANSR	ACTIVE	SO	NS	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	74LV244A	Samples
SN74LV244APWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244APWRE4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244APWRG3	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244APWRG4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples
SN74LV244APWT	OBSOLETE	TSSOP	PW	20		TBD	Call TI	Call TI	-40 to 125	LV244A	
SN74LV244ARGYR	ACTIVE	VQFN	RGY	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LV244A	Samples
SN74LV244ARKSR	ACTIVE	VQFN	RKS	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV244A	Samples

 $<sup>^{(1)}</sup>$  The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE**: TI has discontinued the production of the device.

## PACKAGE OPTION ADDENDUM

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(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF SN74LV244A:

Automotive: SN74LV244A-Q1

Enhanced Product: SN74LV244A-EP

#### NOTE: Qualified Version Definitions:

- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications



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## TAPE AND REEL INFORMATION



## 

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV244ADBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74LV244ADBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74LV244ADGSR	VSSOP	DGS	20	5000	330.0	16.4	5.4	5.4	1.45	8.0	16.0	Q1
SN74LV244ADGVR	TVSOP	DGV	20	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV244ADWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74LV244ADWR	SOIC	DW	20	2000	330.0	24.4	10.9	13.3	2.7	12.0	24.0	Q1
SN74LV244ANSR	so	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74LV244APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LV244APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LV244APWRG3	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN74LV244APWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LV244APWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LV244ARGYR	VQFN	RGY	20	3000	330.0	12.4	3.8	4.8	1.6	8.0	12.0	Q1
SN74LV244ARKSR	VQFN	RKS	20	3000	180.0	12.4	2.8	4.8	1.2	4.0	12.0	Q1



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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV244ADBR	SSOP	DB	20	2000	353.0	353.0	32.0
SN74LV244ADBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN74LV244ADGSR	VSSOP	DGS	20	5000	356.0	356.0	35.0
SN74LV244ADGVR	TVSOP	DGV	20	2000	356.0	356.0	35.0
SN74LV244ADWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LV244ADWR	SOIC	DW	20	2000	356.0	356.0	41.0
SN74LV244ANSR	so	NS	20	2000	367.0	367.0	45.0
SN74LV244APWR	TSSOP	PW	20	2000	353.0	353.0	32.0
SN74LV244APWR	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LV244APWRG3	TSSOP	PW	20	2000	364.0	364.0	27.0
SN74LV244APWRG4	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LV244APWRG4	TSSOP	PW	20	2000	353.0	353.0	32.0
SN74LV244ARGYR	VQFN	RGY	20	3000	356.0	356.0	35.0
SN74LV244ARKSR	VQFN	RKS	20	3000	210.0	185.0	35.0





## NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

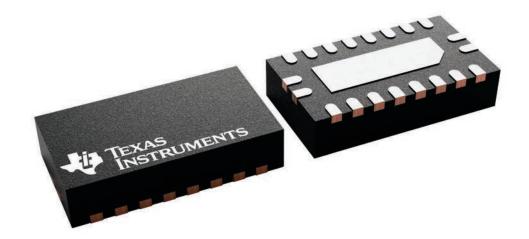
- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



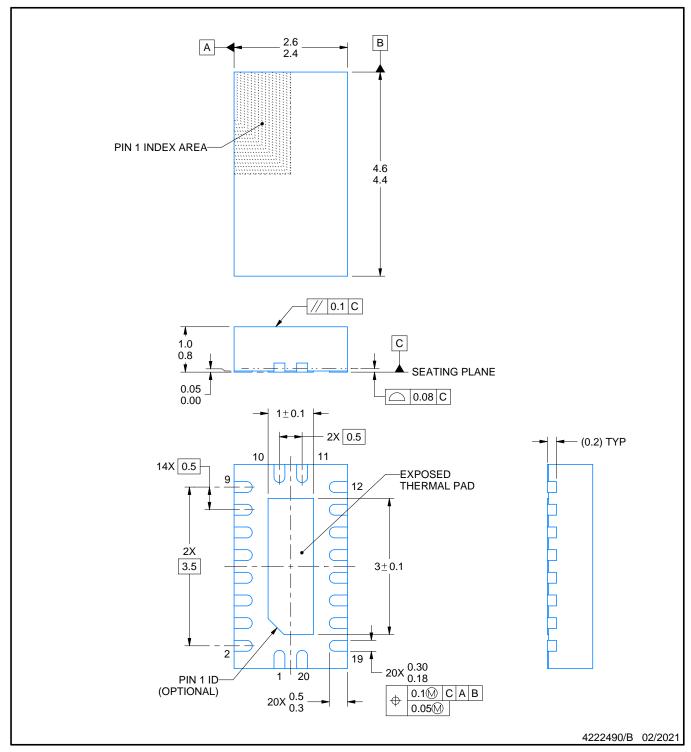
2.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



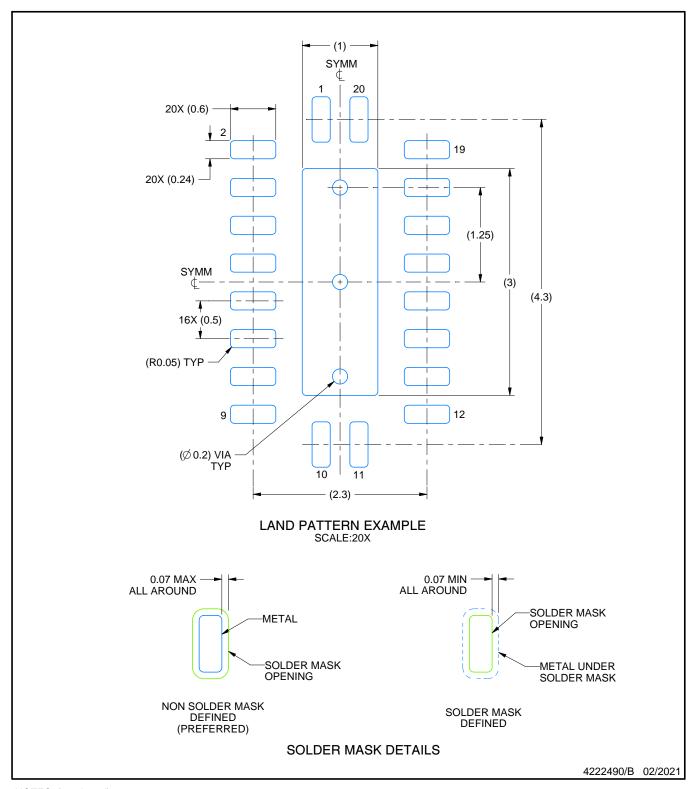




#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

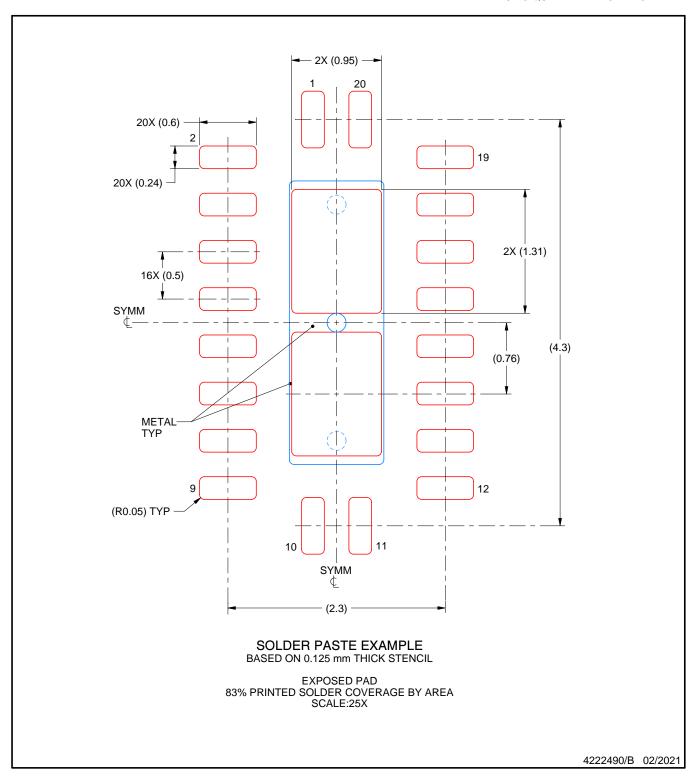




NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.





NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



## **MECHANICAL DATA**

## NS (R-PDSO-G\*\*)

# 14-PINS SHOWN

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



3.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FGLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.





NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.





NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SOIC



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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